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UNITED STATES PATENT AND TRADEMARK OFFICE

To re the Application of: MITSUCHI FUJIIKI Group Art Unit: 2823
Application Number: 10/772,283 Examiner: Thanh V. Pham
Filed: February 6, 2008 Confirmation Number: 6481

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
INCLUDING A LOW-TEMPERATURE LOWER
ELECTRODE-FORMING STEP

Attorney docket Number: 882868
Customer Number: 38834

DECLARATION UNDER 37 C.F.R. § 1.132

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date Filed: 

Sir:

- I, Mitsuchi Fujiki, a citizen of Japan, hereby declare and state the following:
1. I graduated from Osaka University of Osaka, Japan in 1996 with a Ph.D. degree in Science.
 2. Since 1997, I have been employed by Fujitsu Limited of Kawasaki, Japan where my present title is engineer of FeRAM development. During my employment there, I have conducted research and development of processing for FeRAM.
 3. I am the author of the following publications:
M.Fujiki et al., Integrated Ferroelectrics, 26, [1-4] 269-275 (1999).
J.S.Cheon et al., Jpn. J. Appl. Phys., 38, L498-500 (1999).
 4. I have read and am familiar with the above-identified patent application as well as the Official Action dated Aug. 28, 2007, in the application.
 5. I have read and am familiar with the contents of cited references, U.S. Patent Nos. 6,380,634 to Corvesco et al.; 6,344,089 to Sasaki et al.; and 6,568,871 to Massoumi et al. cited in the Official Actions in the above-identified application.